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IRF330-333/IRF730-733 MTM/MTP5N35/5N40 N-Channel Power MOSFETs, 5.5 A, 350 V/400 V

Power And Discrete Division

Description

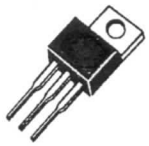
These devices are n-channel, enhancement mode, power MOSFETs designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

- **V_{GS} Rated at ±20 V**
- **Silicon Gate for Fast Switching Speeds**
- **I_{DSS}, $V_{DS(on)}$, SOA and $V_{GS(th)}$ Specified at Elevated Temperature**
- **Rugged**

TO-204AA

IRF330
IRF331
IRF332
IRF333
MTM5N35
MTM5N40

TO-220AB



IRF730
IRF731
IRF732
IRF733
MTP5N35
MTP5N40

Maximum Ratings

Symbol	Characteristic	Rating IRF330/332 IRF730/732 MTM/MTP5N40	Rating IRF331/333 IRF731/733 MTM/MTP5N35	Unit
V_{DSS}	Drain to Source Voltage	400	350	V
V_{DGR}	Drain to Gate Voltage R_{GS} = 1.0 MΩ	400	350	V
V_{GS}	Gate to Source Voltage	±20	±20	V
T_J, T_{stg}	Operating Junction and Storage Temperature	−55 to +150	−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" From Case for 5 s	275	275	°C

Maximum On-State Characteristics

		IRF330/331 IRF730/731	IRF332/333 IRF732/733	MTM5N35/40 MTP5N35/40	
$R_{DS\ (on)}$	Static Drain-to-Source On Resistance	1.0	1.5	1.0	Ω
I_D	Drain Current Continuous Pulsed	 5.5 22	 4.5 22	 5.0 22	A

Maximum Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.67	1.67	1.67	°C/W
P_D	Total Power Dissipation at T_C = 25°C	75	75	75	W

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
$V_{(BR)DSS}$	Drain Source Breakdown Voltage[1]			V	V_{GS} = 0 V, I_D = 250 μA
	IRF330/332/730/732	400			
	IRF331/333/731/733	350			
I_{DSS}	Zero Gate Voltage Drain Current		250	μA	V_{DS} = Rated V_{DSS}, V_{GS} = 0 V
			1000	μA	V_{DS} = 0.8 x Rated V_{DSS}, V_{GS} = 0 V, T_C = 125°C
I_{GSS}	Gate-Body Leakage Current			nA	V_{GS} = ±20 V, V_{DS} = 0 V
	IRF330-333		±100		
	IRF730-733		±500		
On Characteristics					
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	I_D = 250 μA, V_{DS} = V_{GS}
$R_{DS(on)}$	Static Drain-Source On-Resistance[2]			Ω	V_{GS} = 10 V, I_D = 3.0 A
	IRF330/331/730/731		1.0		
	IRF332/333/732/733		1.5		
g_{fs}	Forward Transconductance	3.0		S (℧)	V_{DS} = 10 V, I_D = 3.0 A
Dynamic Characteristics					
C_{iss}	Input Capacitance		900	pF	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz
C_{oss}	Output Capacitance		300	pF	
C_{rss}	Reverse Transfer Capacitance		80	pF	
Switching Characteristics (T_C = 25°C, *Figures 12, 13*)					
$t_{d(on)}$	Turn-On Delay Time		30	ns	V_{DD} = 175 V, I_D = 3.0 A, V_{GS} = 10 V, R_{GEN} = 15 Ω, R_{GS} = 15 Ω
t_r	Rise Time		35	ns	
$t_{d(off)}$	Turn-Off Delay Time		55	ns	
t_f	Fall Time		35	ns	
Q_g	Total Gate Charge		30	nC	V_{GS} = 10 V, I_D = 7.0 A, V_{DD} = 180 V

Symbol	Characteristic	Typ	Max	Unit	Test Conditions
Source-Drain Diode Characteristics					
V_{SD}	Diode Forward Voltage				
	IRF330/331/730/731		1.6	V	I_S = 5.5 A; V_{GS} = 0 V
	IRF332/333/732/733		1.5	V	I_S = 4.5 A; V_{GS} = 0 V
t_{rr}	Reverse Recovery Time	400		ns	I_S = 5.5 A; dI_S/dt = 100 A/μS

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
$V_{(BR)DSS}$	Drain Source Breakdown Voltage[1]			V	V_{GS} = 0 V, I_D = 5.0 mA
	MTM/MTP5N40	400			
	MTM/MTP5N35	350			
I_{DSS}	Zero Gate Voltage Drain Current		0.25	mA	V_{DS} = 0.85 x Rated V_{DSS}, V_{GS} = 0 V
			2.5	mA	V_{DS} = 0.85 x Rated V_{DSS}, V_{GS} = 0 V, T_C = 100°C
I_{GSS}	Gate-Body Leakage Current		±500	nA	V_{GS} = ±20 V, V_{DS} = 0 V
On Characteristics					
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.5	V	I_D = 1.0 mA, V_{DS} = V_{GS}
		1.5	4.0	V	I_D = 1.0 mA, V_{DS} = V_{GS} T_C = 100°C
$R_{DS(on)}$	Static Drain-Source On-Resistance[2]		1.0	Ω	V_{GS} = 10 V, I_D = 2.5 A
$V_{DS(on)}$	Drain-Source On-Voltage[2]		2.5 6.2	V V	V_{GS} = 10 V; I_D = 2.5 A V_{GS} = 10 V, I_D = 5.0 A
			5.0	V	V_{GS} = 10 V, I_D = 2.5 A T_C = 100°C
g_{fs}	Forward Transconductance	2.0		S (℧)	V_{DS} = 10 V, I_D = 2.5 A
Dynamic Characteristics					
C_{iss}	Input Capacitance		1200	pF	V_{DS} = 25 V, V_{GS} = 0 V f = 1.0 MHz
C_{oss}	Output Capacitance		300	pF	
C_{rss}	Reverse Transfer Capacitance		80	pF	
Switching Characteristics (T_C = 25°C, *Figures 12, 13*)[3]					
$t_{d(on)}$	Turn-On Delay Time		50	ns	V_{DD} = 25 V, I_D = 2.5 A V_{GS} = 10 V, R_{GEN} = 50 Ω R_{GS} = 50 Ω
t_r	Rise Time		100	ns	
$t_{d(off)}$	Turn-Off Delay Time		200	ns	
t_f	Fall Time		100	ns	
Q_g	Total Gate Charge		30	nC	V_{GS} = 10 V, I_D = 7.0 A V_{DD} = 180 V

Notes
1. T_J = +25°C to +150°C
2. Pulse test: Pulse width ≤ 80 μs, Duty cycle ≤ 1%
3. Switching time measurements performed on LEM TR-58 test equipment.